TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

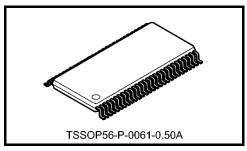
TC74VCX16841FT

Low-Voltage 20-Bit D-Type Latch with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16841FT is a high-performance CMOS 20-bit D-type latch. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to $3.6\ V.$

The TC74VCX16841FT can be used as two 10-bit latches or one 20-bit latch. The 20 latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs. While the latch-enable (1LE or 2LE) input is high, the Q outputs of the corresponding 10-bit latch follow the D inputs. When LE is taken low, the Q outputs are latched at the



Weight: 0.25 g (typ.)

levels set up at the D inputs. When the OE input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.

Features

- Low-voltage operation: $V_{CC} = 1.8 \text{ to } 3.6 \text{ V}$
- High-speed operation: $t_{pd} = 3.0 \text{ ns (max) (V}_{CC} = 3.0 \text{ to } 3.6 \text{ V)}$

 $t_{pd} = 3.4 \text{ ns (max) (VCC} = 2.3 \text{ to } 2.7 \text{ V}$

 $t_{pd} = 6.8 \text{ ns (max) (V}_{CC} = 1.8 \text{ V})$

- Output current: $I_{OH}/I_{OL} = \pm 24$ mA (min) ($V_{CC} = 3.0$ V)
 - $: I_{OH}/I_{OL} = \pm 18 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$
 - $: I_{OH}/I_{OL} = \pm 6 \text{ mA (min) (V}_{CC} = 1.8 \text{ V)}$
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200 \text{ V}$

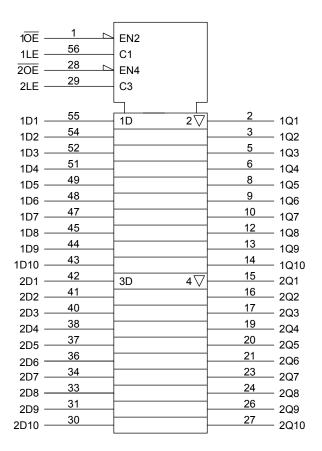
Human body model $\geq \pm 2000 \text{ V}$

- Package: TSSOP
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

Pin Assignment (top view)

10E 56 1LE 1Q1 2 1D1 55 1Q2 3 1D2 54 GND 4 **GND** 53 1Q3 5 1D3 52 1Q4 6 51 1D4 7 V_{CC} 50 V_{CC} 1Q5 8 1D5 49 1Q6 9 48 1D6 1Q7 10 1D7 47 GND 11 46 **GND** 1Q8 12 1D8 45 1Q9 13 1D9 1Q10 14 43 1D10 2Q1 15 42 2D1 2D2 2Q2 16 41 2Q3 17 40 2D3 GND 18 39 **GND** 2D4 2Q4 19 38 2D5 2Q5 20 37 2Q6 21 36 2D6 V_{CC} 22 35 Vcc 2Q7 23 34 2D7 2D8 2Q8 24 33 GND 25 **GND** 32 2Q9 26 2D9 31 2D10 2Q10 27 30 2OE 28 2LE 29

IEC Logic Symbol



Truth Table (each 10-bit latch)

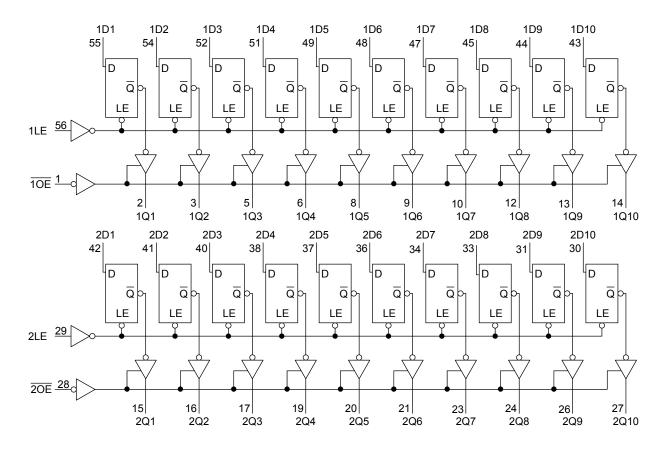
	Output Q		
ŌĒ	LE	D	Q
L	Н	Н	Н
L	Н	L	L
L	L	Х	Qn
Н	Х	Х	Z

X: Don't care

Z: High impedance

Qn: Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram



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Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage	V _{IN}	-0.5 to 4.6	V
		-0.5 to 4.6 (Note 2)	
DC output voltage	V_{OUT}	–0.5 to V _{CC} + 0.5	V
		(Note 3)	
Input diode current	I_{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	lout	±50	mA
Power dissipation	P_{D}	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: OFF state

Note 3: High or low state. $I_{\mbox{\scriptsize OUT}}$ absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	1.8 to 3.6	V	
Tower supply voltage	vCC	1.2 to 3.6 (Note 2)	V	
Input voltage	V _{IN}	-0.3 to 3.6	V	
Output voltage	Vour	0 to 3.6 (Note 3)	V	
Output voltage	V _{OUT}	0 to V _{CC} (Note 4)		
		±24 (Note 5)		
Output current	I _{OH} /I _{OL}	±18 (Note 6)	mA	
		±6 (Note 7)		
Operating temperature	T _{opr}	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V	

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

Note 2: Data retention only

Note 3: OFF state

Note 4: High or low state

Note 5: $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 V$

Note 8: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V



Electrical Characteristics

DC Characteristics (Ta = -40 to 85° C, 2.7 V < $V_{CC} \le 3.6$ V)

Character	Characteristics		Test C	Condition	V 00	Min	Max	Unit
	1				V _{CC} (V)			
Input voltage	H-level	V _{IH}	-	_	2.7 to 3.6	2.0		V
	L-level	V_{IL}	-		2.7 to 3.6	_	0.8	
				$I_{OH} = -100 \mu A$	2.7 to 3.6	V _{CC} - 0.2	_	
	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -12 \text{ mA}$	2.7	2.2	_	
				$I_{OH} = -18 \text{ mA}$	3.0	2.4	_	
Output voltage				$I_{OH} = -24 \text{ mA}$	3.0	2.2	_	V
		V _{OL}	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 100 \mu A$	2.7 to 3.6	_	0.2	
	L-level			I _{OL} = 12 mA	2.7	_	0.4	
	L-ievei			I _{OL} = 18 mA	3.0	_	0.4	
				I _{OL} = 24 mA	3.0	_	0.55	
Input leakage curre	ent	I _{IN}	V _{IN} = 0 to 3.6 V	•	2.7 to 3.6	_	±5.0	μА
0 -1-11-1-055	-1-1	loz	V _{IN} = V _{IH} or V _{IL}					
3-state output OFF	3-state output OFF state current		$V_{OUT} = 0$ to 3.6 V		2.7 to 3.6	_	±10.0	μΑ
Power-off leakage	current	l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА
Outgoognt gunsty			V _{IN} = V _{CC} or GND		2.7 to 3.6	_	20.0	
Quiescent supply of	unent	Icc	V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7 to 3.6	_	±20.0	μА
Increase in I _{CC} per	input	Δlcc	$V_{IH} = V_{CC} - 0.6 V$		2.7 to 3.6	_	750	

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characte	ristics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
	H-level	V _{IH}		_	2.3 to 2.7	1.6	_	
Input voltage	L-level	V _{IL}		_	2.3 to 2.7	_	0.7	V
				I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	_	
	H-level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -6 mA	2.3	2.0	_	
		011		I _{OH} = -12 mA	2.3	1.8	_	V
Output voltage				I _{OH} = -18 mA	2.3	1.7	_	
		level V _{OL}	OL VIN = VIH or VIL	I _{OL} = 100 μA	2.3 to 2.7	_	0.2	
	L-level			I _{OL} = 12 mA	2.3	_	0.4	
				I _{OL} = 18 mA	2.3	_	0.6	
Input leakage curre	ent	I _{IN}	V _{IN} = 0 to 3.6 V	•	2.3 to 2.7	_	±5.0	μА
2 state output OFF	= atata aurrant	la-	$V_{IN} = V_{IH}$ or V_{IL}		2.3 to 2.7		. 40.0	
3-state output OFF state current		loz	V _{OUT} = 0 to 3.6 V		2.3 10 2.7	_	±10.0	μΑ
Power-off leakage	current	loff	V _{IN} , V _{OUT} = 0 to 3.6 V		0		10.0	μА
0.:		loo	$V_{IN} = V_{CC}$ or GND		2.3 to 2.7		20.0	μА
Quiescent supply	Current	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le$	3.6 V	2.3 to 2.7	_	±20.0	μΑ



DC Characteristics (Ta = -40 to 85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteristics		Symbol	Test Co	andition		Min	Max	Unit
Ondraotene	71100	Cymbol	1001 00	Test Condition		IVIIII	Wax	Offic
Input voltage	H-level	V _{IH}	_	_	1.8 to 2.3	$\begin{array}{c} 0.7 \times \\ V_{CC} \end{array}$		V
input voltage	L-level	V _{IL}	_	_	1.8 to 2.3	_	0.2 × V _{CC}	V
	H-level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	V
Output voltage				I _{OH} = -6 mA	1.8	1.4	_	
	l. laval	lovol V-	OL VIN = VIH or VIL	$I_{OL} = 100 \mu A$	1.8		0.2	
	L-level	VOL		I _{OL} = 6 mA	1.8		0.3	
Input leakage currer	nt	I _{IN}	$V_{IN} = 0$ to 3.6 V		1.8		±5.0	μΑ
3-state output OFF	state current	loz	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 3.6 \text{ V}$		1.8	_	±10.0	μА
Power-off leakage c	urrent	l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА
0.1		laa	V _{IN} = V _{CC} or GND		1.8		20.0	μА
Quiescent supply cu	iii c iii	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8		±20.0	μА

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AC Characteristics (Ta = –40 to 85°C, input: $t_r = t_f$ = 2.0 ns, C_L = 30 pF, R_L = 500 Ω) (Note 1)

Characteristics	Symbol	Symbol Test Condition		Min M		Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	IVIIII	Wax	Offic
Propagation delay time	+		1.8	1.5	6.8	
(D-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	1.0	3.4	ns
(D-Q)	t _{pHL}		3.3 ± 0.3	0.8	3.0	
Dran a gation delay time			1.8	1.5	8.8	
Propagation delay time	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	1.0	4.4	ns
(LE-Q)	t _{pHL}		3.3 ± 0.3	0.8	3.5	
			1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	1.0	4.9	ns
	t _{pZH}		3.3 ± 0.3	0.8	3.8	
			1.8	1.5	7.6	ns
3-state output disable time	t _{pLZ}	Figure 1, Figure 3	2.5 ± 0.2	1.0	4.2	
			3.3 ± 0.3	0.8	3.7	
M: 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		Figure 1, Figure 2	1.8	4.0		ns
Minimum pulse width	t _{W (H)}		2.5 ± 0.2	1.5		
(LE)			3.3 ± 0.3	1.5		
			1.8	2.5		
Minimum setup time	ts	Figure 1, Figure 2	2.5 ± 0.2	1.5		ns
			3.3 ± 0.3	1.5		
			1.8	1.0		
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0		ns
		-	3.3 ± 0.3	1.0	_	
	,		1.8	_	0.5	
Output to output skew	t _{osLH}	(Note 2)	2.5 ± 0.2	_	0.5	ns
	tosHL		3.3 ± 0.3	_	0.5	

Note 1: For $C_L = 50 \ pF$, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$



Dynamic Switching Characteristics

(Ta = 25°C, input: $t_r = t_f = 2.0 \text{ ns}, C_L = 30 \text{ pF}, R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition			Тур.	Unit
	,			V _{CC} (V)	,.	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote)	1.8	0.25	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote)	2.5	0.6	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote)	3.3	8.0	
	V _{OLV}	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote)	1.8	-0.25	٧
Quiet output minimum dynamic V _{OI}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote)	2.5	-0.6	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote)	3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote)	1.8	1.5	
Quiet output minimum dynamic V _{OH}		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (N	lote)	3.3	2.2	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

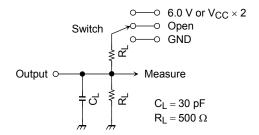
Characteristics	Symbol	Test Condition		V _{CC} (V)	Тур.	Unit
lanut conscitores	-				0	
Input capacitance	C _{IN}	-		1.8, 2.5, 3.3	б	pF
Output capacitance	C _{OUT}	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$	(Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/20 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

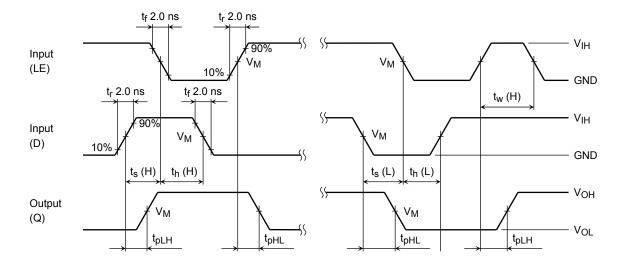


Figure 2 t_{pLH} , t_{pHL} , t_w , t_s , t_h

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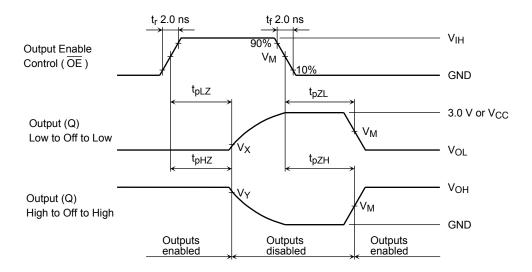


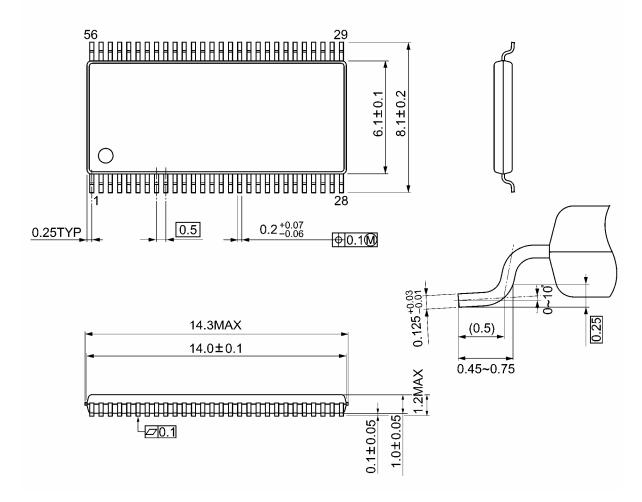
Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	Vcc						
Syllibol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V				
V _{IH}	2.7 V	V _{CC}	V _{CC}				
V _M	1.5 V	V _{CC} /2	V _{CC} /2				
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V				
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V				

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Package Dimensions

TSSOP56-P-0061-0.50A Unit: mm



Weight: 0.25 g (typ.)

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20070701-EN GENERAL

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